

40V NPN LOW SATURATION TRANSISTOR IN SOT23

Features

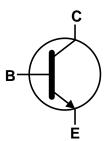
- BV_{CEO} > 40V
- I_C = 2A high Continuous Collector Current
- I_{CM} = 3A Peak Pulse Current
- Low Saturation Voltage 180mV Max @ I_C = 1A
- R_{CE(SAT)} = 60mΩ at 0.5A for a Low Equivalent On-Resistance
- 730mW Power Dissipation
- Complimentary PNP Type: DSS5240T
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

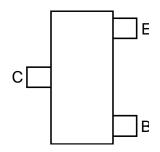
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.008 grams (Approximate)







Device Symbol



Top View Pin Configuration

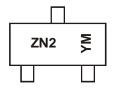
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DSS4240T-7	ZN2	7	8	3,000
DSS4240T-13	ZN2	13	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen and Antimony free, "Green" and Lead-Free.
- 3. Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZN2 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: C = 2015) M = Month (ex: 9 = September)

Date Code Key

Year	2013	2014	2015	2016	2017	2018	3 201	19 2	020	2021	2022	2023
Code	Α	В	С	D	Е	F	G	;	Н		J	K
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	40	V
Collector-Emitter Voltage	V_{CEO}	40	V
Emitter-Base Voltage	V_{EBO}	5	V
Peak Pulse Collector Current	I _{CM}	3	A
Continuous Collector Current	Ic	2	A
Peak Base Current	I _{BM}	0.3	A

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P _D	730	mW
Power Dissipation (Note 6)	P _D	600	mW
Thermal Resistance, Junction to Ambient Air (Note 5)	$R_{ hetaJA}$	171	°C/W
Thermal Resistance, Junction to Ambient Air (Note 6)	$R_{ heta JA}$	209	°C/W
Thermal Resistance, Junction to Lead (Note 7)	$R_{ heta JL}$	75	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 8)

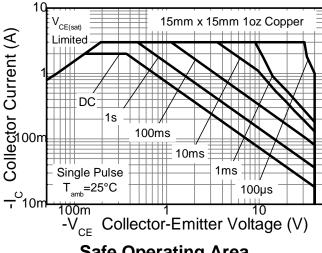
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

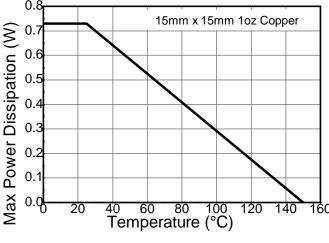
Notes:

- 5. For a device mounted with the collector lead on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as note (5), except the device is mounted on minimum recommended pad layout.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



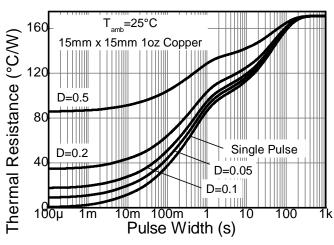
Thermal Characteristics and Derating Information

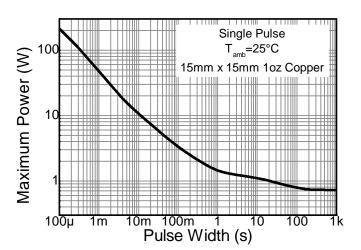












Transient Thermal Impedance

Pulse Power Dissipation

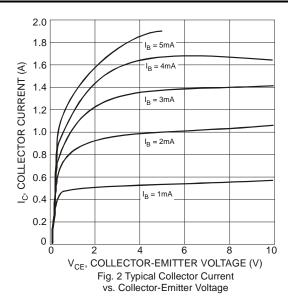


Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	40	_	_	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV_{CEO}	40	_	_	V	I _C = 10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	5	_	_	V	I _E = 100μA
Collector-Base Cutoff Current	lone			100	nA	$V_{CB} = 30V, I_{E} = 0$
Collector-base Cutoff Current	I _{CBO}		_	50	μΑ	$V_{CB} = 30V$, $I_E = 0$, $T_A = +150$ °C
Emitter-Base Cutoff Current	I _{EBO}			100	nA	$V_{EB} = 4V, I_{C} = 0$
ON CHARACTERISTICS (Note 9)						
		350	_	_		$V_{CE} = 2V, I_{C} = 0.1A$
DC Current Gain	L	300	_	_		$V_{CE} = 2V, I_{C} = 0.5A$
DC Current Gain	h _{FE}	300		_		V _{CE} = 2V, I _C = 1A
		150		_		$V_{CE} = 2V$, $I_C = 2A$
				70		$I_C = 100 \text{mA}, I_B = 1 \text{mA}$
			30	100		$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}			180	mV	$I_C = 750 \text{mA}, I_B = 15 \text{mA}$
			_	180		I _C = 1A, I _B = 50mA
				320		$I_C = 2A$, $I_B = 200mA$
Equivalent On-Resistance	R _{CE(sat)}		60	200	mΩ	$I_C = 500 \text{mA}, I_B = 50 \text{mA}$
Base-Emitter Saturation Voltage	V _{BE(sat)}		_	1.1	V	$I_C = 2A$, $I_B = 200mA$
Base-Emitter Turn-on Voltage	V _{BE(on)}	_	_	0.75	V	V _{CE} = 2V, I _C = 100mA
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f _T	100	_	_	MHz	$V_{CE} = 10V, I_{C} = 100mA,$ f = 100MHz
Output Capacitance	C _{ob}	_	_	20	pF	V _{CB} = 10V, f = 1MHz

Note:

Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



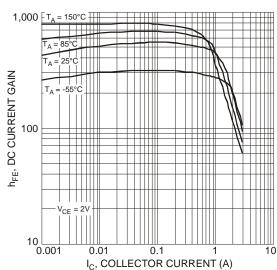


Fig. 3 Typical DC Current Gain vs. Collector Current

^{9.} Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.



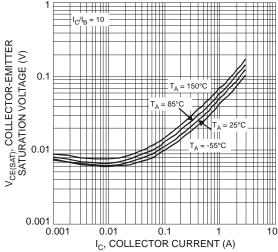


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

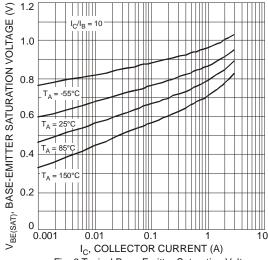


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current

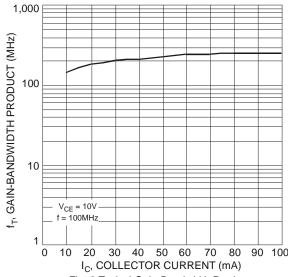


Fig. 8 Typical Gain-Bandwidth Product vs. Collector Current

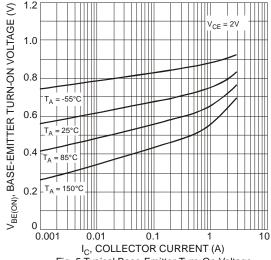


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current

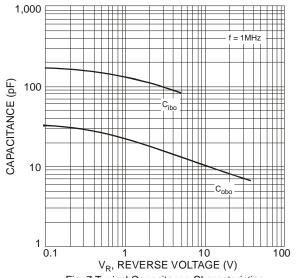
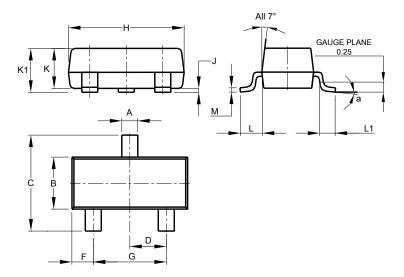


Fig. 7 Typical Capacitance Characteristics



Package Outline Dimensions

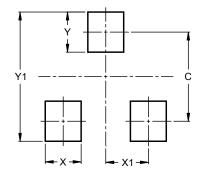
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT23							
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
М	0.085	0.150	0.110				
а	0°	8°					
All	All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Y	0.9
Y1	2.9



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